


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Applicants	:	Kaori TAN)	Customer No.
Appln. No.	:	09/639,163)	
Filed	:	August 16, 2000)	26694
For	:	METHOD OF PRODUCING SEMICONDUCTOR DEVICES USING A HYDROGEN PEROXIDE (as amended))	PATENT TRADEMARK OFFICE
Examiner	:	Coleman)	
Art Unit	:	2823)	
Atty. Dkt.	:	32011-165642)	

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action of October 7, 2002, please amend this application
as follows:

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A method of producing semiconductor devices by cobalt
silicide technology with titanium nitride film as the cap film, comprising: